3DK10

NPN Silicon High Frequency Middle Power Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							Test Condition
			A	B	C	D	E	F	G	
Total Dissipation	P_{tot}	mW	1500							Ta=25°C
Max. Collector Current	I_{CM}	mA	1000							
Junction Temperature	T_{jm}	°C	175							
Storage Temperature	T_{stg}	°C	-55~+175							
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	25	40	60	75	100	75	60	I_C=0.1mA
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	20	30	45	60	80	60	40	
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	4							I_E=0.1mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.5							I_C=600mA, I_B=60mA
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	1.2							
C-E Leakage Current	I_{CEO}	uA	10					3		V_{CE}=15V
E-B Leakage Current	I_{EBO}	uA	1.0							V_{EB}=1.5V
DC Current Gain	h_{FE}		Orange: 25~40, Yellow: 40~55, Green: 55~80 Blue: 80~120, Purple: 120~180							V_{CE}=2V, I_C=60mA
Transition frequency	f_T	MHz	150							V_{CE}=10V, I_C=150mA f=30MHz
Turn-on Time	t_{on}	ns	30							I_C=300mA I_{B1}= I_{B2}=30mA
Storage Time	t_s	ns	270							
Fall Time	t_f	ns	30							

Outline and Dimensions: